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US 20050239241 A1	US- PGPUB	20051027	High speed lateral heterojunction MISFETS realized by 2-dimensional bandgap engineering and methods thereof	438/197	438/199	Ouyang, Qiqing Christine et al.
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US 20020185686 A1	US- PGPUB	20021212	Relaxed SiGe layers on Si or silicon-on-insulator substrates by ion implantation and thermal annealing	257/347	257/E21.125; 257/E21.129; 257/E21.561; 257/E21.567	Christiansen, Silke H. et al.
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US 6943407 B2	USPAT	20050913	Low leakage heterojunction vertical transistors and high performance devices thereof	257/329	257/351; 257/E21.63 3; 257/E21.64 3; 438/153; 438/213 Ouyang; QiQing Christine et al.

US 6927414 B2	USPAT	20050809	High speed lateral heterojunction MISFETs realized by 2-dimensional bandgap engineering and methods thereof	257/20	257/19; 257/190; 257/194; 257/E21.63 3; 257/E21.63 4; 257/E29.08 5; 257/E29.31 5; 438/172; 438/933	Ouyang; Qiqing Christine et al.
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US 6900687 B2	USPAT	20050531	Circuitry and method to provide a high speed comparator for an input stage of a low-voltage differential signal	327/478	327/53	Saint-Luc; Olivier A. et al.

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US 6858502 B2	USPAT	20050222	High speed composite p-channel Si/SiGe heterostructure for field effect devices	438/285	257/E29.04 9; 257/E29.05 6; 257/E29.24 8; 438/172	Chu; Jack Oon et al.
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US 6855649 B2	USPAT	20050215	Relaxed SiGe layers on Si or silicon-on-insulator substrates by ion implantation and thermal annealing	438/311	257/E21.125; 257/E21.129; 257/E21.561; 257/E21.567; 438/933	Christiansen; Silke H. et al.
US 6843181 B2	USPAT	20050118	Ducting associated with rail track and installing apparatus	104/275	174/68.1; 238/2; 238/8	Morris; Jonathan Mark
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US 6815802 B2	USPAT	20041109	Incorporation of carbon in silicon/silicon germanium epitaxial layer to enhance yield for Si-Ge bipolar technology	257/592	257/12; 257/19; 257/55; 257/565; 257/616; 257/63; 257/E21.371; 257/E29.193	Chu; Jack Oon et al.
US 6805962 B2	USPAT	20041019	Method of creating high-quality relaxed SiGe-on-insulator for strained Si CMOS applications	428/446	257/347; 257/349; 257/E21.129; 257/E21.145; 257/E21.324; 257/E21.448; 257/E21.563; 428/220; 428/336; 428/450; 428/498; 428/641	Bedell; Stephen W. et al.
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US 6750119 B2	USPAT	20040615	Epitaxial and polycrystalline growth of Si _{1-x-y} Ge _x C _y and Si ₁₋	438/479	427/249.1; 427/255.28 ; 438/483	Chu; Jack Oon et al.

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US 6743651 B2	USPAT	20040601	Method of forming a SiGe-on-insulator substrate using separation by implantation of oxygen	438/46	257/E21.56 3; 438/149; 438/235; 438/311; 438/312; 438/47; 438/966; 438/967	Chu; Jack O. et al.
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US 6709903 B2	USPAT	20040323	Relaxed SiGe layers on Si or silicon-on-insulator substrates by ion implantation and thermal annealing	438/149	257/E21.12 5; 257/E21.12 9; 257/E21.56 1; 257/E21.56 7; 438/77; 438/938	Christiansen; Silke H. et al.
US 6690072 B2	USPAT	20040210	Method and structure for ultra-low contact resistance CMOS formed by vertically self-aligned CoSi2	257/382	257/377; 257/412; 257/55; 257/616; 257/65; 257/754;	Cabral, Jr.; Cyril et al.

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US 6649492 B2	USPAT	20031118	Strained Si based layer made by UHV-CVD, and devices therein	438/478	257/E21.129; 257/E21.448; 257/E21.569; 257/E21.57; 257/E29.286; 257/E29.295; 438/459; 438/479; 438/483	Chu; Jack O. et al.
US 6593625 B2	USPAT	20030715	Relaxed SiGe layers on Si or silicon-on-insulator substrates by ion implantation and thermal annealing	257/347	257/12; 257/E21.125; 257/E21.129; 257/E21.561; 257/E21.567	Christiansen; Silke H. et al.
US 6527401 B1	USPAT	20030304	Electroluminescent lighting device	362/84	362/217	Chu; Jackson Luk Wah
US 6524935 B1	USPAT	20030225	Preparation of strained Si/SiGe on insulator by hydrogen induced layer transfer technique	438/478	257/E21.568; 438/458; 438/479; 438/507	Canaperi; Donald F. et al.
US 6512705 B1	USPAT	20030128	Method and apparatus for standby power reduction in semiconductor devices	365/189.11	365/229; 365/230.03	Koelling; Jeff et al.
US 6475072	USPAT	20021105	Method of wafer	451/65	257/E21.23	Canaperi;

B1			smoothing for bonding using chemo-mechanical polishing (CMP)		; 257/E21.24 4; 257/E21.30 4; 257/E21.56 7; 451/285	Donald F. et al.
US 6426265 B1	USPAT	20020730	Incorporation of carbon in silicon/silicon germanium epitaxial layer to enhance yield for Si-Ge bipolar technology	438/312	257/E21.37 1; 257/E29.19 3; 438/357	Chu; Jack Oon et al.
US 6425951 B1	USPAT	20020730	Advance integrated chemical vapor deposition (AICVD) for semiconductor	117/3	117/88; 117/89; 117/93	Chu; Jack Oon et al.
US 6391461 B1	USPAT	20020521	Adhesion of paint to thermoplastic olefins	428/424.8	427/407.1; 427/412.3; 428/423.1; 428/424.2; 428/483; 428/515; 428/520	Ryntz; Rose Ann et al.
US 6377764 B1	USPAT	20020423	Method and apparatus for communication, without a solid medium, among control boards in a printing apparatus	399/75		Morris-jones; Stephen
US 6350993 B1	USPAT	20020226	High speed composite p-channel Si/SiGe heterostructure for field effect devices	257/19	257/18; 257/190; 257/191; 257/192; 257/20; 257/E29.04 9; 257/E29.05 6; 257/E29.24 8	Chu; Jack Oon et al.
US 6341875	USPAT	20020129	Decorative lighting	362/252	362/653;	Chu; Jack

B1			assembly		362/806; 439/210; 439/509	Shao-Chun
US 6251751 B1	USPAT	20010626	Bulk and strained silicon on insulator using local selective oxidation	438/439	257/352; 257/55; 257/63; 257/750; 257/E21.56 4; 438/400; 438/410	Chu; Jack Oon et al.
US D431897 S	USPAT	20001017	Shoe upper	D2/969	D2/902; D2/907	Morris; Jonathan et al.
US 6096590 A	USPAT	20000801	Scalable MOS field effect transistor	438/233	257/E27.06 8; 438/301; 438/586	Chan; Kevin Kok et al.
US 6062132 A	USPAT	20000516	Cooking apparatus	99/404	99/407; 99/408; 99/409; 99/416	Morris; Jonathan Emrys
US 6059895 A	USPAT	20000509	Strained Si/SiGe layers on insulator	148/33.1	148/33.4; 148/33.5; 257/19; 257/190; 257/E21.12 2; 257/E21.12 5; 257/E21.12 9; 257/E21.56 7	Chu; Jack Oon et al.
US 6013134 A	USPAT	20000111	Advance integrated chemical vapor deposition (AICVD) for semiconductor devices	118/715	118/719; 118/724; 414/938; 414/939	Chu; Jack Oon et al.
US D418005 S	USPAT	19991228	Cooking device	D7/338	D7/350.1	Morris; Jonathan Emrys
US 5963817 A	USPAT	19991005	Bulk and strained silicon on insulator using local selective oxidation	438/410	257/E21.56 4; 438/439	Chu; Jack Oon et al.
US 5906951	USPAT	19990525	Strained Si/SiGe	438/751	257/E21.12	Chu; Jack

A			layers on insulator		2; 257/E21.12 5; 257/E21.12 9; 257/E21.56 7; 438/752; 438/753	Oon et al.
US 5809568 A	USPAT	19980922	Disposable bibs	2/49.1	2/52	Morris-Jones; Muriel
US 5780327 A	USPAT	19980714	Vertical double-gate field effect transistor	438/156	257/E29.27 4; 257/E29.28 1; 438/268	Chu; Jack Oon et al.
US 5755646 A	USPAT	19980526	Adjustable clothes hanging and exercising apparatus	482/118	482/115	Chu; Jack Shao-Chun
US D391050 S	USPAT	19980224	Shoe upper	D2/970		Morris; Jonathan R.
US 5689127 A	USPAT	19971118	Vertical double-gate field effect transistor	257/329	257/135; 257/263; 257/328; 257/E21.41 ; 257/E29.26 2; 257/E29.27 4	Chu; Jack Oon et al.
US D385395 S	USPAT	19971028	Shoe upper	D2/969	D2/970	Morris; Jonathan
US D383595 S	USPAT	19970916	Shoe upper	D2/970	D2/969	Morris; Jonathan R.
US D382389 S	USPAT	19970819	Shoe upper	D2/969		Morris; Jonathan R.
US 5656514 A	USPAT	19970812	Method for making heterojunction bipolar transistor with self-aligned retrograde emitter profile	438/320	257/197; 257/198; 257/E21.37 1; 438/317; 438/936	Ahlgren; David et al.
US D380291 S	USPAT	19970701	Element of a shoe	D2/972		Morris; Jonathan R.
US 5638882 A	USPAT	19970617	Venetian blind ladder carrier	160/176.1R		Morris; Jonhn E.

			mechanism			
US 5634973 A	USPAT	19970603	Low temperature selective growth of silicon or silicon alloys	117/95	257/E21.13 1	Cabral, Jr.; Cyril et al.
US D378550 S	USPAT	19970325	Shoe upper	D2/970		Morris; Jonathan R.
US 5600090 A	USPAT	19970204	Filter for electrical apparatus	174/17VA	150/154; 150/165; 206/320; 361/687	Morris; Jonathan
US 5595600 A	USPAT	19970121	Low temperature selective growth of silicon or silicon alloys	148/33.3	117/932; 257/E21.13 1; 438/945	Cabral, Jr.; Cyril et al.
US 5565031 A	USPAT	19961015	Method for low temperature selective growth of silicon or silicon alloys	117/95	117/935; 148/DIG.1 06; 257/E21.13 1; 438/488; 438/945	Cabral, Jr.; Cyril et al.
US 5433872 A	USPAT	19950718	Cable grease composition and articles incorporating same	508/136	385/100; 523/173	Brauer; Melvin et al.
US 5427630 A	USPAT	19950627	Mask material for low temperature selective growth of silicon or silicon alloys	148/33.2	117/95; 257/E21.13 1; 438/488; 438/945	Cabral, Jr.; Cyril et al.
US D357574 S	USPAT	19950425	Shoe upper	D2/970	D2/969	Morris; Jonathan R.
US 5385850 A	USPAT	19950131	Method of forming a doped region in a semiconductor substrate utilizing a sacrificial epitaxial silicon layer	438/372	257/E21.15 1; 257/E21.37 5; 438/558	Chu; Jack O. et al.
US 5385497 A	USPAT	19950131	Water exerciser	441/129	114/352; 440/21	Chu; Jack S.
US 5384152 A	USPAT	19950124	Method for forming capacitors with roughened single crystal plates	438/386	117/108; 257/309; 257/E21.01 3; 257/E29.34 5;	Chu; Jack C. et al.

					427/255.15; 427/255.18; 427/255.7; 427/419.1; 427/79; 427/80; 427/81; 438/398; 438/964	
US D353038 S	USPAT	19941206	Footwear upper	D2/969	D2/916	Morris; Jonathan R. et al.
US D352162 S	USPAT	19941108	Shoe upper	D2/970		Morris; Jonathan R.
US D346897 S	USPAT	19940517	Shoe upper	D2/970	D2/912	Morris; Jonathan R. et al.
US D346486 S	USPAT	19940503	Shoe upper	D2/969	D2/912; D2/970	Morris; Jonathan R. et al.
US 5286334 A	USPAT	19940215	Nonselective germanium deposition by UHV/CVD	117/97	117/936	Akbar; Shahzad et al.
US D342147 S	USPAT	19931214	Shoe upper	D2/970		Morris; Jonathon R.
US 5266504 A	USPAT	19931130	Low temperature emitter process for high performance bipolar devices	438/364	117/8; 148/DIG.1; 148/DIG.1 24; 257/E21.13 1; 257/E21.13 3; 257/E21.37 1; 257/E21.37 9; 438/365	Blouse; Jeffrey L. et al.
US 5259918 A	USPAT	19931109	Heteroepitaxial growth of germanium on silicon by UHV/CVD	117/90	117/935; 117/936; 117/97; 438/753	Akbar; Shahzad et al.
US 5245206	USPAT	19930914	Capacitors with	257/309	257/190;	Chu; Jack O.

A			roughened single crystal plates		257/301; 257/68; 257/E21.01 3; 257/E29.34 5	et al.
US D325292 S	USPAT	19920414	Shoe upper	D2/969		Morris; Jonathan R. et al.
US D323925 S	USPAT	19920218	Shoe upper	D2/970		Brown; Paul D. et al.
US 4918783 A	USPAT	19900424	Adjustable wheel structure	16/19	16/32; 280/43.17; 280/43.2	Chu; Jack
US 1722853 A	USPAT	19290730	Dust hood for buffing machines [TEXT AVAILABLE IN USOCR DATABASE]	451/456	29/DIG.85	MORRIS JONAH W